

# HA16129FPJ Single Watchdog Timer

REJ03F0144-0300 (Previous: ADE-204-027B) Rev.3.00 Jun 15, 2005

### Description

The HA16129FPJ is a watchdog timer IC that monitors a microprocessor for runaway. In addition to the watchdog timer function, the HA16129FPJ also provides a function for supplying a high-precision stabilized power supply to the microprocessor, a power on reset function, a power supply voltage monitoring function, and a fail-safe function that masks the microprocessor outputs if a runaway is detected.

### **Functions**

- Watchdog timer (WDT) function Monitors the P-RUN signal output by the microprocessor, and issues an auto-reset (RES) signal if a microprocessor runaway is detected.
- Stabilized power supply Provides power to the microprocessor.
- Power on and clock off functions The power on function outputs a low level signal to the microprocessor for a fixed period when power is first applied.

The clock off function outputs a RES signal to the microprocessor a fixed period after a runaway occurs.

- Power supply monitoring function
   When the reference voltage (Vout) falls and becomes lower than the <u>NMI</u> detection voltage (4.63 V, Typ) or the <u>STBY</u> detection voltage (3.0 V Typ), this function outputs either an <u>NMI</u> signal or an <u>STBY</u> signal, respectively. Note that NMI detection can be set to monitor either V<sub>CC</sub> or Vout.
- OUTE function<sup>\*1</sup> (fail-safe function) Outputs a signal used to mask microprocessor outputs when a microprocessor runaway has been detected.
- RES delay function Sets the delay between the time the NMI signal is output and the time the RES signal is output.
- Protection functions
   The HA16129FPJ incorporates both Vout overvoltage prevention and current limiter functions.

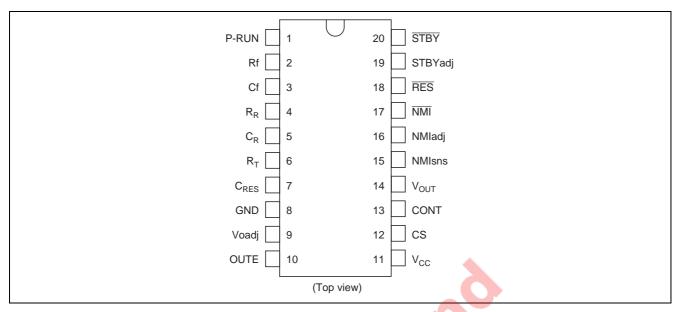
Note: 1. OUTE function: OUTE is an abbreviation for output enable.

### Features

- High-precision output voltage:  $5.0 \text{ V} \pm 1.5\%$
- The WDT supports both frequency and duty detection schemes.
- High-precision power supply monitoring function:  $4.625 \text{ V} \pm 0.125 \text{ V}$
- Built-in OUTE function
- All functions can be adjusted with external resistors and/or capacitors.

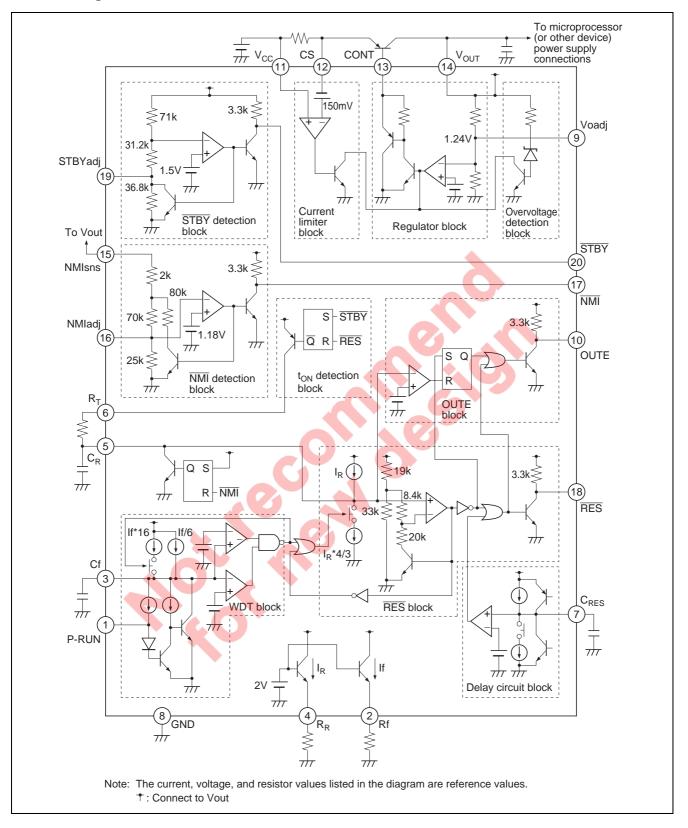


#### **Pin Arrangement**





### **Block Diagram**





## **Pin Function**

Related	Pin		
Function	No.	Symbol	Function
WDT.	1	P-RUN	Watchdog timer pulse input. The auto-reset function is controlled by the duty cycle or frequency of this input pulse signal.
	2	Rf	The resistor connected to this pin determines the current that flows in the Cf pin capacitor. Use the resistor value from $100 \text{ k}\Omega$ to $500 \text{ k}\Omega$
	3	Cf	The current determined by the Rf pin charges the Cf capacitor and the potential on this pin determines the watchdog timer frequency band.
$t_{\rm RH},t_{\rm RL},t_{\rm OFF}$	4	R <sub>R</sub>	The resistor connected to this pin determines the current that flows in the $C_R$ pin capacitor. Use the resistor value from 100 k $\Omega$ to 500 k $\Omega$
	5	C <sub>R</sub>	The current determined by the $R_R$ pin charges the capacitor $C_R$ and the potential on this pin controls the $\overline{\text{RES}}$ function (toff, $t_{RH}$ , and $t_{RL}$ ).
t <sub>on</sub>	6	R <sub>T</sub>	The resistor R <sub>T</sub> , which determines only the time t <sub>ON</sub> for the RES function is connected to this pin. This resistor determines the current that charges the capacitor C <sub>R</sub> for the time t <sub>ON</sub> . Use the resistor value from 100 k $\Omega$ to 500 k $\Omega$
tr, t <sub>RES</sub>	7	C <sub>RES</sub>	The current determined by the Rf pin charges the capacitor $C_{RES}$ , and the RES delay times (Tr and $T_{RES}$ ) are determined by the potential of this capacitor.
_	8	GND	Ground
Vout	9	Voadj	Insert the resistor Roadj if fine adjustment of the regulator output voltage Vout is required. Leave this pin open if Vout does not need to be changed.
Output	10	OUTE	Output for the OUTE function
Power supply	11	V <sub>cc</sub>	Power supply
Current limiter	12	CS	Current limiter detection. Connect the overcurrent detection resistor between the CS pin and the V <sub>CC</sub> pin. If this function is not used, short this pin to V <sub>CC</sub> . Also, connect this pin to the emitter of the external transistor. (This function can not operate when $V_{OUT} \le 2$ V)
Vout	13	CONT	Connect this pin to the base of the external transistor.
	14	V <sub>OUT</sub>	Provides the regulator output voltage and the IC internal power supply. Connect this pin to the collector of the external transistor.
NMI	15	NMIsns	This pin senses the $\overline{\text{NMI}}$ detection voltage. If V <sub>CC</sub> is to be detected, connect this pin to the V <sub>CC</sub> pin (however, note that an external resistor is required), and if Vout is to be detected, connect this pin to the V <sub>OUT</sub> pin.
	16	NMladj	Insert a resistor if fine adjustment of the NMI detection voltage is required.
Output	17	NMI	NMI         output
Output	18	RES	RES output
STBY	19	STBYadj	Insert a resistor if fine adjustment of the STBY detection voltage is required. Leave this pin open if fine adjustment is not required.
Output	20	STBY	STBY output



### **Functional Description**

This section describes the functions provided by the HA16129FPJ. See the section on formulas for details on adjustment methods.

#### **Regulator Block**

• Vout Voltage

This IC provides a stabilized 5 V power supply by controlling the base current of an external transistor. The largest current (the maximum CONT pin current) that can be drawn by the base of this external transistor is 20 mA. Also note that the Vout output is also used for the power supply for this IC's internal circuits.

#### **Current Limiter Block**

When a current detection resistor ( $R_{CS}$ ) is connected between the  $V_{CC}$  pin and the CS pin, and the voltage between these pins exceeds the  $V_{CS}$  voltage (150 mV Typ), the CONT pin function turns off and the output voltage supply is stopped. This function can not work when  $V_{OUT} < 2$  V.

Note: This function is not short detection.

#### **Output Voltage (Vout) Adjustment**

The output voltage can be adjusted by connecting an external resistor at the output voltage adjustment pin (Voadj). However, if for some reason the voltage on this Vout line increases and exceeds the voltage adjustment range (7 V Max), the CONT pin function turns off and the output voltage supply is stopped.

Refer to the timing charts in conjunction with the following items.

#### LVI (Low Voltage Inhibit)

• **NMI** Detection Voltage

This function monitors for drops in the power-supply voltage. This function can be set up to monitor either  $V_{CC}$  or Vout. When Vout is monitored, a low level is output from the  $\overline{NMI}$  pin if that voltage falls under the detection voltage (4.63 V Typ). Then, when the power-supply voltage that fell rises again, the  $\overline{NMI}$  pin will output a high level. Note that this function has a fixed hysteresis of 50 mV (Typ). The monitored power supply is selected by connecting the NMIsns pin either to the  $V_{CC}$  pin or to the  $V_{OUT}$  pin. When detecting  $V_{CC}$ , an external adjustment resistor is required.)

The detection voltage can also be adjusted with the NMIadj pin.

• <u>STBY</u> Detection Voltage

This function monitors for drops in the Vout voltage. It monitors the Vout voltage, and outputs a low level from the STBY pin if that voltage drops below the detection voltage (3.0 V Typ). Then, when the power-supply voltage that fell rises again, the STBY pin will output a high level. Note that this function has a fixed hysteresis of 1.35 V (Typ). The detection voltage can also be adjusted with the STBYadj pin.

#### **Function Start Voltage**

This is the minimum required Vout voltage for the  $\overline{\text{RES}}$ ,  $\overline{\text{NMI}}$ ,  $\overline{\text{STBY}}$ , and OUTE output pin functions to start operating. It is stipulated as the voltage that Vout must reach after power is first applied for these pins to output a low level.

#### **Hysteresis**

This is the difference between the LVI function detection voltage when the power-supply voltage drops, and the clear (reset) voltage when the power-supply voltage rises.

 $(V_{HYSN} = V_{NMI}' - V_{NMI}; V_{HYSS} = V_{STBY}' - V_{STBY})$ 



#### **OUTE Function**

When a microprocessor is in the runaway state, its outputs are undefined, and thus it is possible that the outputs may be driven by incorrect signals. This function is used to mask such incorrect microprocessor outputs. When the WDT function recognizes normal operation (when the  $\overline{\text{RES}}$  output is high), the OUTE output will be held high. When the WDT function recognizes an abnormal state and an auto-reset pulse is output from the  $\overline{\text{RES}}$  pin, the OUTE output will be held low. Thus microprocessor outputs during microprocessor runaway can be masked by taking the AND of those outputs and this signal using external AND gates.

The OUTE output will go high when the  $C_R$  pin voltage exceeds VthHcr2, and will go low when that voltage falls below VthLcr.

There are limitation that apply when the OUTE function is used. Refer to the calculation formulas item for details.

#### **RES** Function

• t<sub>RH</sub>

This period is the length of the high-level output period of the  $\overline{\text{RES}}$  pulse when the P-RUN signal from the microprocessor stops. This is the time required for the C<sub>R</sub> potential to reach VthLcr from VthHcr1.

• t<sub>RL</sub>

This period is the length of the low-level output period of the  $\overline{\text{RES}}$  pulse when the P-RUN signal from the microprocessor stops. This is the time required for the C<sub>R</sub> potential to reach VthHcr1 from VthLcr.

• t<sub>OFF</sub>

This is the time from the point the P-RUN signal from the microprocessor stops to the point a low level is output from the  $\overline{\text{RES}}$  pin. During normal microprocessor operation, the potential on the C<sub>R</sub> pin will be about Vout – 0.2 V (although this value may change with the P-RUN signal input conditions, so it should be verified in the actual application circuit) and t<sub>OFF</sub> is the time for the C<sub>R</sub> pin potential to reach VthLcr from that potential.

• t<sub>ON</sub>

 $t_{ON}$  is the time from the point the  $\overline{NMI}$  output goes high when power is first applied to the point the  $\overline{RES}$  output goes low.  $t_{ON}$  is the time for the potential of the  $C_R$  pin to reach VthHcr1 from 0 V.

• tr

The time tr is the fixed delay time between the point the  $\overline{\text{NMI}}$  output goes from low to high after the power-supply voltage comes up to the point  $\overline{\text{RES}}$  goes from low to high. The time tr is the time for the CRES pin potential to fall from the high voltage (about 1.9 V) to V theres.

The time  $t_{RES}$  is the fixed delay time between the point the  $\overline{NMI}$  output goes from high to low when the powersupply voltage falls to the point  $\overline{RES}$  goes from high to low. The time  $t_{RES}$  is the time for the  $C_{RES}$  pin potential to rise from 0 V to Vtheres.

#### **WDT Function**

This function determines whether the microprocessor is operating normally or has entered a runaway state by monitoring the duty or frequency of the P-RUN signal. When this function recognizes a runaway state, it outputs a reset pulse from the RES pin and sets the OUTE pin to low from high. It holds the RES and OUTE pins fixed at high as long as it recognizes normal microprocessor operation.

In this function, the potential of the Cf capacitor is controlled by the P-RUN signal. This Cf pin potential charges the capacitor  $C_R$  that controls the reset pulse to be between VthLcf and VthHcf. The judgment as to whether or not the microprocessor is operating normally, is determined by the balance between the charge and discharge voltage on the capacitor  $C_R$  at this time.



<sup>•</sup> t<sub>RES</sub>

## **Calculation Formulas**

Item	Formula	Notes				
Reference	→ → → → → → → → → → → → → → → → → → →	While the Vout voltage will be 5 V $\pm 1.5\%$ when the Voadj				
voltage	Vout = 1.225 $\left(1 + \frac{37 // R1}{12 // R2}\right)$	pin is open, the circuit shown here should be used to change				
	R1, R2; kΩ	the Vout voltage externally.				
		$ \begin{array}{c} \hline  \\  \\  \\  \\  \\  \\  \\  \\  \\  \\  \\  \\  \\ $				
Current	$V_{cs}$ (150 mV Typ) < $I_L \cdot R_{cs}$	When this function operates, the base current to the external				
limiter		transistor connected to the CS pin stops and the Vout output				
voltage		is lowered.				
		R <sub>CS</sub> IL T V <sub>CC</sub> CS Vout				
OVP	—	This function prevents the microprocessor from being				
		damaged if the Vout voltage is inadvertently increased to too				
		high a level. The OVP detection voltage is fixed.				
t <sub>RH</sub> , t <sub>RL</sub>	$t_{_{RH}} = 3.3 \times C_{_{R}} \cdot R_{_{R}}$	These determine the reset pulse frequency and duty.				
	$t_{\text{RL}} = 1.1 \times C_{\text{R}} \cdot R_{\text{R}}$					
t <sub>on</sub>	$t_{on} = 1.1 \times C_R \cdot R_T$	Sets the time from the rise of the NMI signal to the point the RES output is cleared.				
	.0					
t <sub>OFF</sub>	$t_{OFF} = 6.5 \times C_R \cdot R_R$	Sets the time from the point the P-RUN pulse stops to the				
		point a reset pulse is output.				
		P-RUN				
	60	RES				



## Calculation Formulas (cont.)

Item	Formula	Notes
V <sub>STBY</sub>	$V_{\text{STBY}} = 1.48 \times \left(\frac{67.6}{29.5 + 36.2  //  \text{R1}} + 1\right)$	The voltage at which the STBY signal is output when Vout falls. The STBY detection voltage can be adjusted by connecting a resistor between the STBYadj pin and ground (R3). However, the STBY recovery voltage cannot be adjusted.
V <sub>NMI</sub> (Vout detection)	$V_{\text{NMI}} = 1.2 \times \left(1 + \frac{\text{R1} //73}{\text{R2} //25}\right)$ R1, R2; k $\Omega$	The voltage at which the $\overline{\text{NMI}}$ signal is output when Vout falls. (When NMIsns is connected to Vout.) The $\overline{\text{NMI}}$ detection voltage can be adjusted by connecting resistors between the NMIadj pin and Vout (R1), and between the NMIadj pin and ground (R2).
V <sub>NMI</sub> (V <sub>CC</sub> detection)	$V_{NMI} = 4.62 \times \left(\frac{R1}{R2 // 97.1} + 1\right)$ Recovery voltage $V_{NMI} = 4.68 \times \left(\frac{R1}{R2 // 45.5} + 1\right)$ R1, R2; kΩ	The voltage at which the $\overline{NMI}$ signal is output when $V_{CC}$ falls. (When NMIsns is connected to $V_{CC}$ .) The $\overline{NMI}$ detection voltage can be adjusted by connecting resistors between the NMIsns pin and $V_{CC}$ (R1), and between the NMIsns pin and ground (R2).
OUTE	$C_R \times R_R > 19.3 \times Cf \times Rf$	If the OUTE function is used, the relationship shown at the left must be fulfilled to assure that pulses are not incorrectly generated in this output when a microprocessor runaway state is detected.



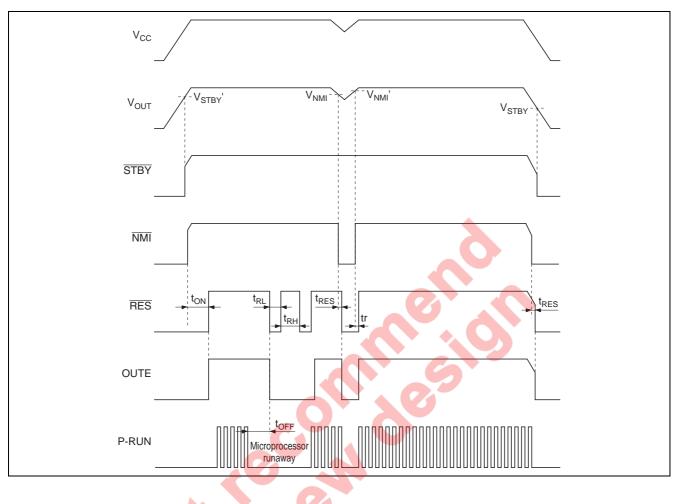
## Calculation Formulas (cont.)

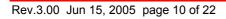
Item	Formula	Notes
f f f f f	$f_{Line1} = \frac{0.31 \times (Du - 24)}{Cf \cdot Rf}$ $f_{Line2} = 24\% \text{ (fixed)}$ $f_{Line3} = \frac{0.024}{Cf \cdot Rf}$ $f_{Line4} = 99\%$ The relationship between $f_{Line1} = f_{Line3} \times 12.9 \text{ (Du - 24)}$ Du: The P-RUN signal duty cycle $\underbrace{t_{H} + t_{L}}_{t_{H} + t_{L}} = Du = \frac{t_{H}}{t_{H} + t_{L}} \times 100$	The WDT function judges whether the P-RUN pulse signal is normal or not. If the WDT function judges the P-RUN pulse signal to be abnormal, it outputs a reset signal. The normal range is the area enclosed by $f_{Line1}$ to $f_{Line4}$ in the figure.



## **Timing Charts**

## Whole system timing chart

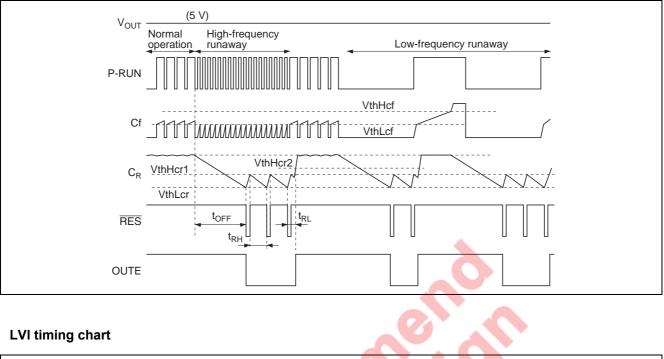


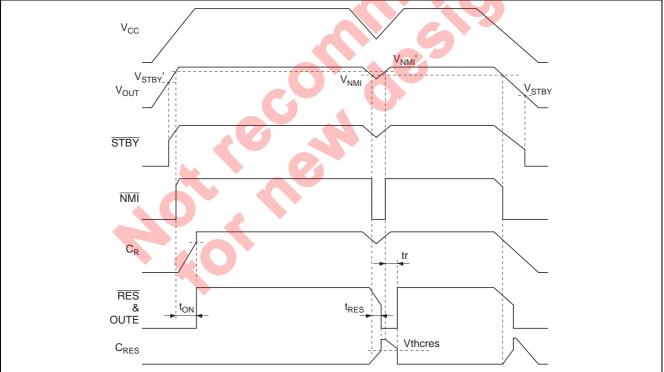


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### WDT. timing chart



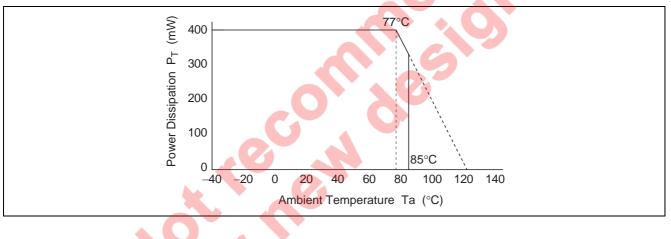




## **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Rating	Unit
Power supply voltage	V <sub>CC</sub>	40	V
CS pin voltage	V <sub>CS</sub>	V <sub>cc</sub>	V
CONT pin current	Icont	20	mA
CONT pin voltage	Vcont	Vcc	V
Vout pin voltage	Vout	12	V
P-RUN pin voltage	VPRUN	Vout	V
NMIsns pin voltage	V <sub>NMIsns</sub>	Vcc	V
NMI pin voltage	V <sub>NMI</sub>	Vout	V
STBY pin voltage	V <sub>STBY</sub>	Vout	V
RES pin voltage	V <sub>RES</sub>	Vout	V
OUTE pin voltage	VOUTE	Vout	V
Power dissipation <sup>*1</sup>	PT	400	mW
Operating temperature	Topr	-40 to +85	٥°
Storage temperature	Tstg	-50 to +125	°C

Note: 1. This is the allowable value when mounted on a 40 × 40 × 1.6 mm glass-epoxy printed circuit board with a mounting density of 10% at ambient temperatures up to Ta = 77°C. This value must be derated by 8.3 mW/°C above that temperature.





### **Electrical Characteristics**

 $(Ta = 25^{\circ}C, V_{CC} = 12V, Vout = 5.0V, Rf = R_{R} = 180k\Omega, Cf = 3300pF, C_{R} = 0.1\mu F, R_{T} = 390k\Omega, C_{RES} = 1500pF, R_{CS} = 0.2\Omega)$ 

	14	O was had	N41	<b>T</b>	Maria	11	$R_{\rm CS} = 0.2\Omega)$
Item		Symbol	Min	Тур	Max	Unit	Test Conditions
Power supply current		I <sub>CC</sub>	_	10	15	mA	
Current limiter voltage		V <sub>CS</sub>	100	150	200	mV	V <sub>CS</sub> = (V <sub>CC</sub> pin voltage – CS pin voltage)
Regulator block	Output voltage	Vout	4.925	5.00	5.075	V	V <sub>CC</sub> = 12V, Icont = 5mA
	Input voltage stabilization	Volin	-30	_	30	mV	V <sub>CC</sub> = 6 to 17.5V, Icont = 10mA
	Load current stabilization	Voload	-30	-	30	mV	lcont = 0.1 to 15mA
	Ripple exclusion ratio	R <sub>REJ</sub>	(45)	75		dB	Vi = 0.5Vrms, fi = 1kHz
	Output voltage temperature coefficient	δVout/δT	-	40	(200)	ppm/°C	Icont = 5mA
	Output voltage adjustment range	V <sub>omax</sub>	-	0	7.0	V	
P-RUN	Input high-level voltage	V <sub>iH</sub>	2.0			V	
input block	Input low-level voltage	V <sub>iL</sub>	-	<u> </u>	0.8	V	
	Input high-level current	I <sub>iH</sub>		300	500	μΑ	V <sub>iH</sub> = 5.0V
	Input low-level current	l <sub>iL</sub>	-5	0	5	μΑ	$V_{iL} = 0.0V$
NMI output block	High level	V <sub>OHN</sub>	Vout – 0.2	Vout	Vout + 0.2	V	I <sub>OHN</sub> = 0mA
	Low level	V <sub>OLN</sub>		_	0.4	V	$I_{OLN}$ = 2.0mA
	Function start voltage	V <sub>STN</sub>	-	0.7	1.4	V	
STBY	High level	V <sub>OHS</sub>	Vout – 0.2	Vout	Vout + 0.2	V	I <sub>OHS</sub> = 0mA
output block	Low level	Vols	-	-	0.4	V	I <sub>OLS</sub> = 2.0mA
	Function start voltage	V <sub>STS</sub>	_	0.7	1.4	V	

Note: Values in parentheses are design reference values.



## Electrical Characteristics (cont.)

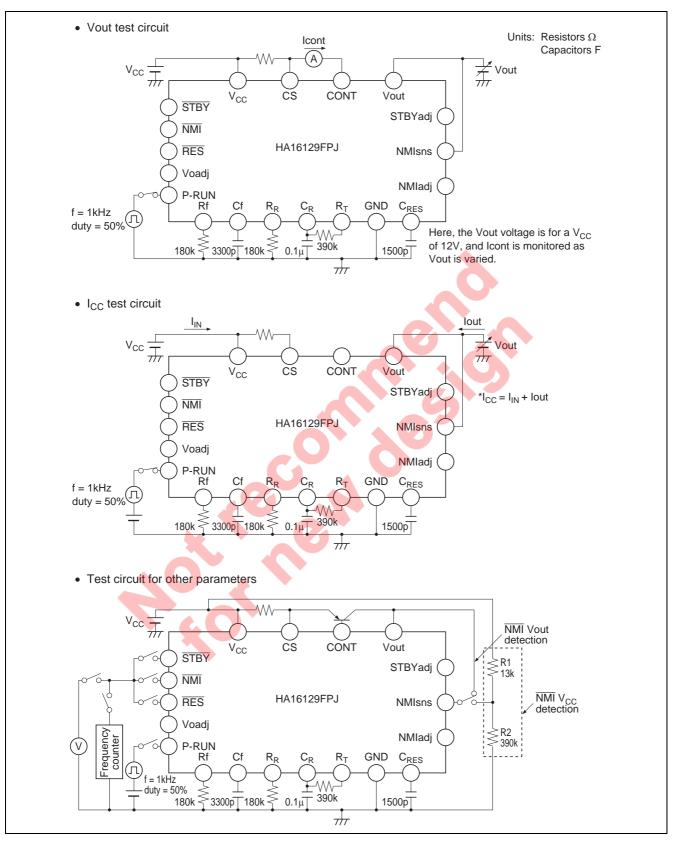
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				-	-		-	$R_{\rm CS} = 0.2\Omega$ )
ltem		Symbol	Min	Тур	Мах	Unit	Test Conditions	
RES	High level		V <sub>OHR</sub>	Vout – 0.2	Vout	Vout + 0.2	V	I <sub>OHR</sub> = 0mA
output	Low level		V <sub>OLR</sub>	-	_	0.4	V	I <sub>OLR</sub> = 2.0mA
block	Function sta	rt voltage	V <sub>STR</sub>	-	0.7	1.4	V	
OUTE	High level		V <sub>OHE</sub>	Vout - 0.2	Vout	Vout + 0.2	V	I <sub>OHE</sub> = 0mA
output	Low level	Low level		-	-	0.4	V	I <sub>OLE</sub> = 2.0mA
block	Function sta	rt voltage	V <sub>STE</sub>	-	0.7	1.4	V	
RES	Power on time		ton	25	40	60	ms	
function	Clock off tim	Clock off time		80	130	190	ms	
	Reset pulse high time		t <sub>RH</sub>	40	60	90	ms	
	Reset pulse low time		t <sub>RL</sub>	15	20	30	ms	
LVI function	NMI function (Vout detection)	Detection voltage 1	V <sub>NMI1</sub>	4.5	4.63	4.75	V	
		Hysteresis 1	V <sub>HYSN1</sub>	_	50	100	mV	
		Temperature coefficient	δV <sub>NMI</sub> /δT	-	100	(400)	ppm/°C	
	NMI function (V <sub>cc</sub> detection)	Detection voltage 2	V <sub>NMI2</sub>	5.0	5.4	5.7	V	R1 = 13kΩ, R2 = 390kΩ
		Hysteresis 2	V <sub>HYSN2</sub>	0.5	0.8	1.3	V	R1 = 13kΩ, R2 = 390kΩ
	STBY function	Detection voltage	V <sub>STBY</sub>	2.70	3.00	3.30	V	
		Hysteresis	V <sub>HYSS</sub>	1.20	1.35	1.50	V	
		Temperature coefficient	δV <sub>STBY</sub> /δT		100	(400)	ppm/°C	
RES	Disable time		t <sub>RES</sub>	(100)	200	(300)	μs	
delay time	time Recovery time		tr	(100)	200	(300)	μs	

Note: Values in parentheses are design reference values.

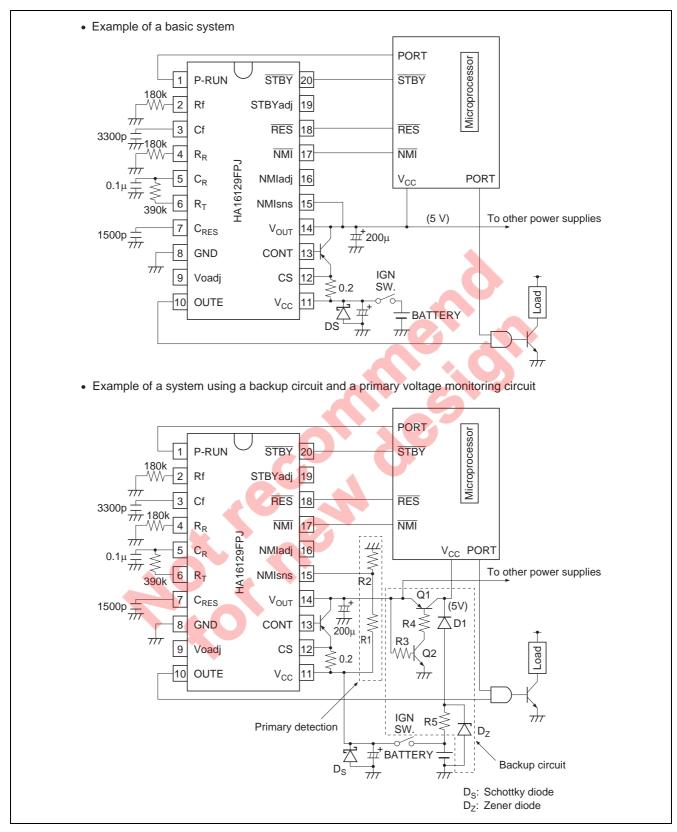


### **Test Circuits**



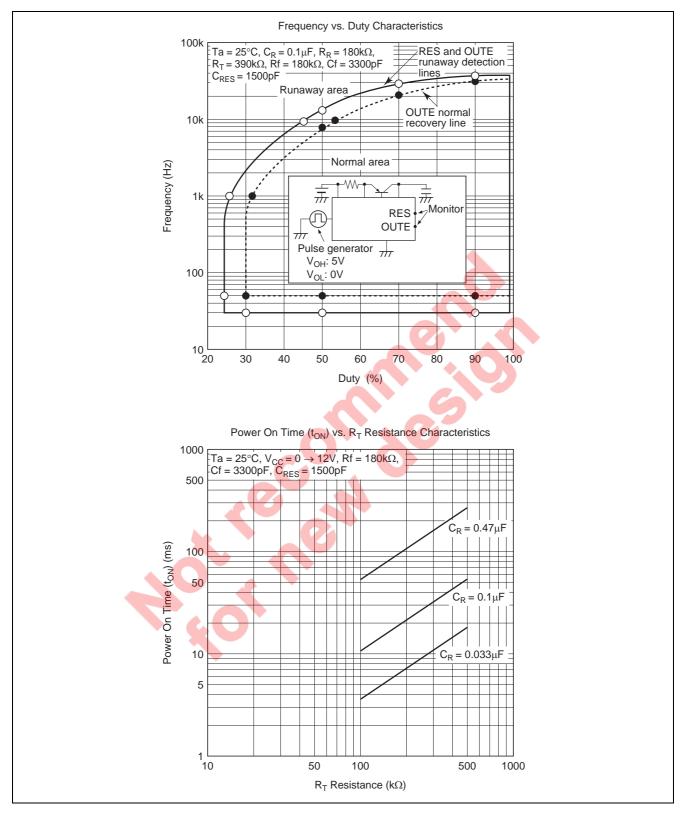


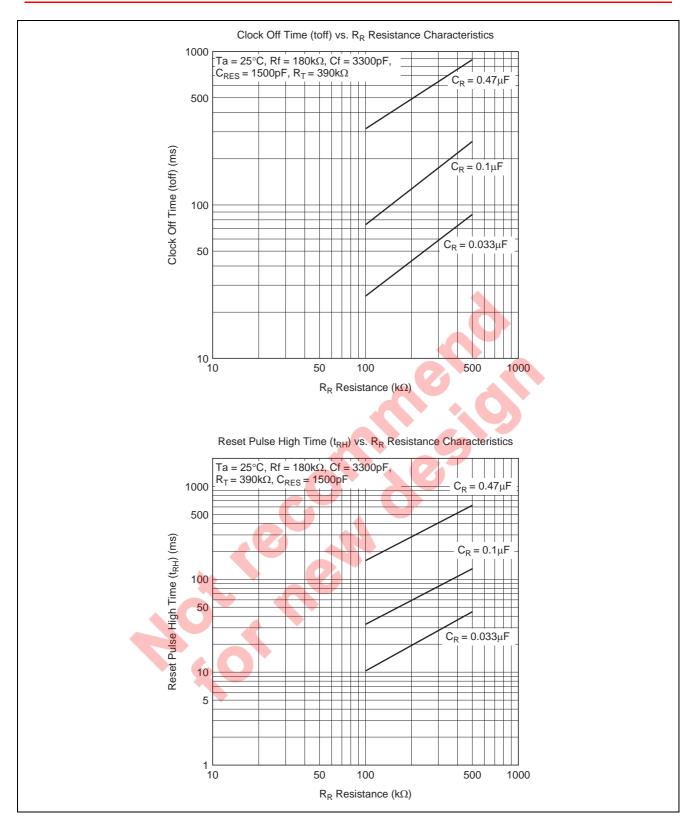
## System Circuit Examples

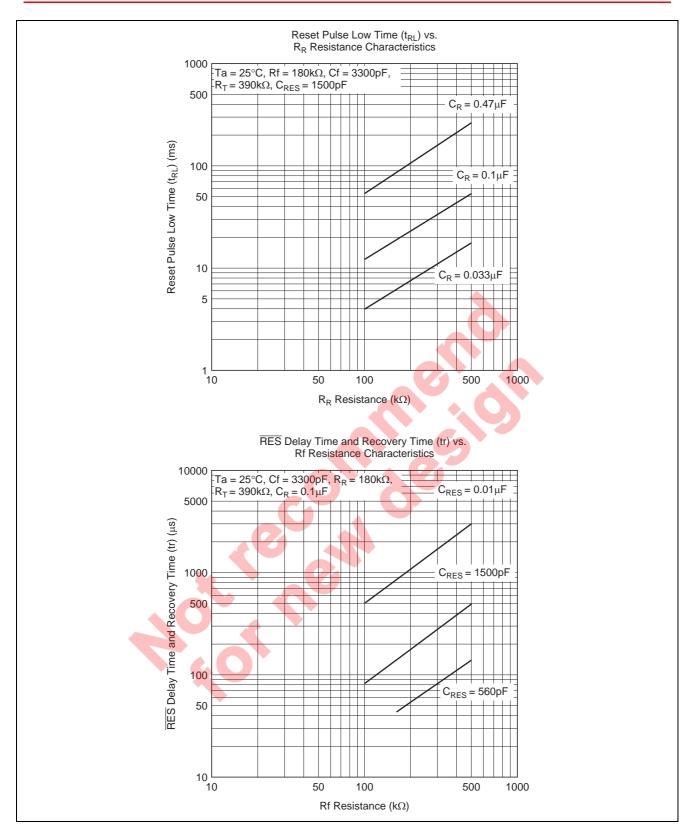




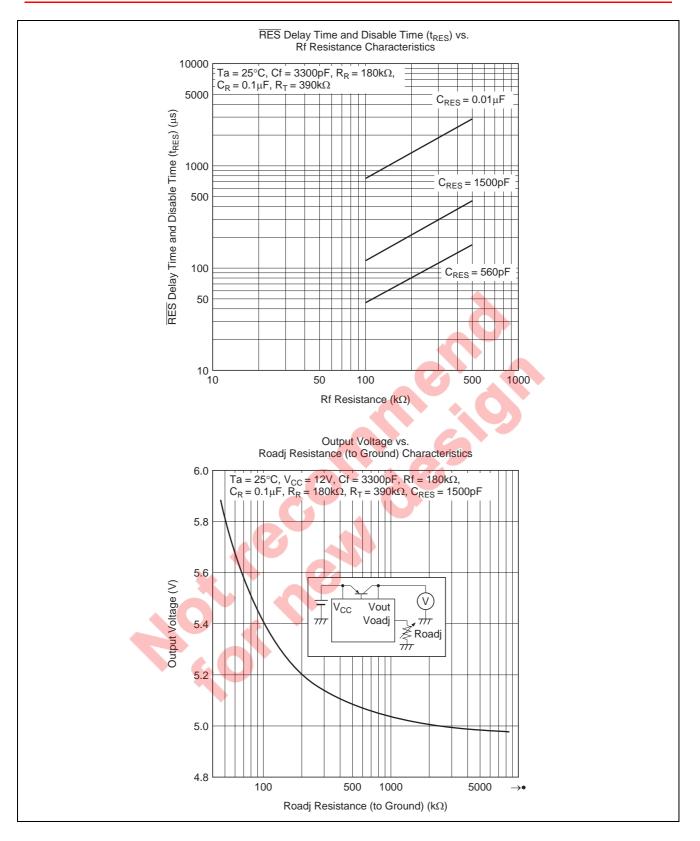
## **Operating Waveforms**

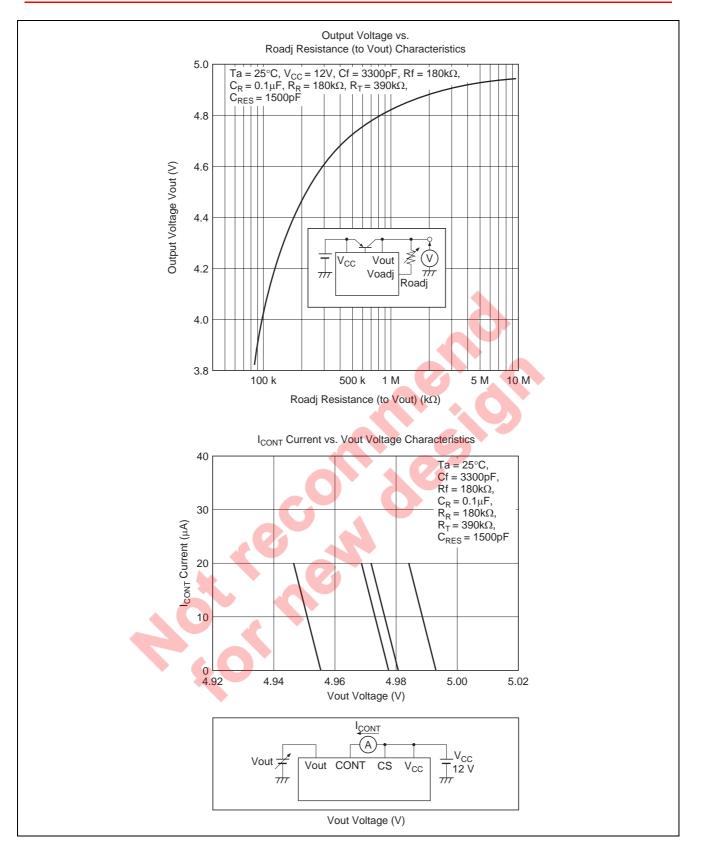




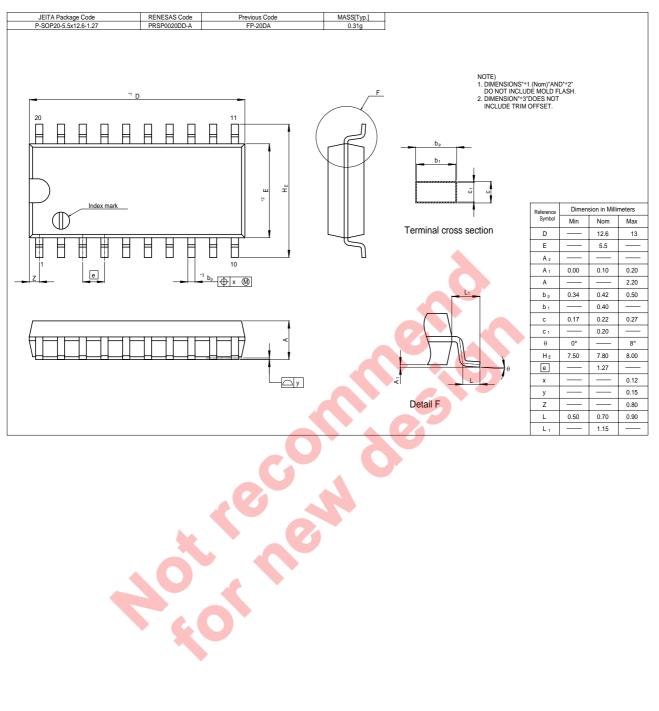


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### **Package Dimensions**





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